

描述 / Descriptions

TO-92 塑封封装 PNP 半导体三极管。
 Silicon PNP transistor in a TO-92 Plastic Package.

特征 / Features

低电流, 低电压。
 Low current, Low voltage.

用途 / Applications

用于一般放大。
 General purpose amplifier.

引脚排列 / Pinning


PIN1 : Collector

PIN 2 : Base

PIN 3 : Emitter

内部等效电路 / Equivalent Circuit

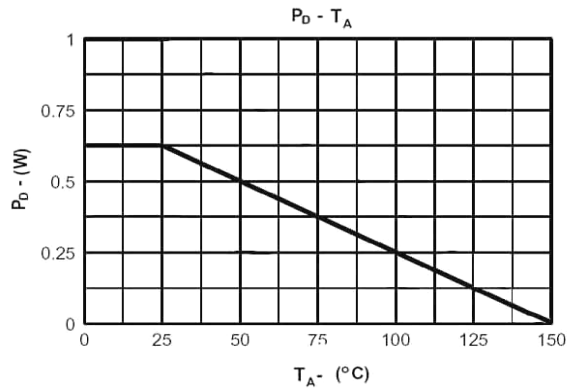
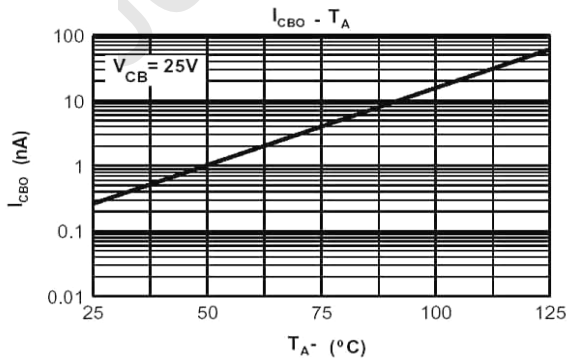
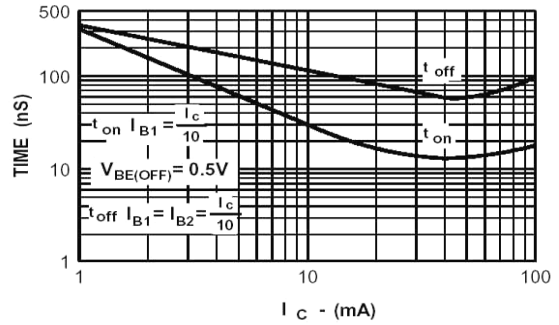
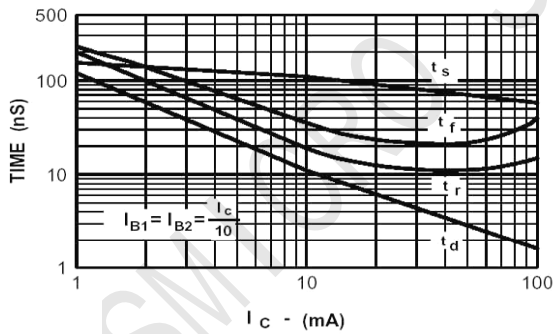
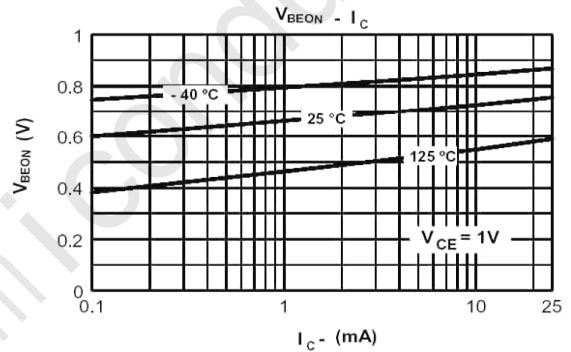
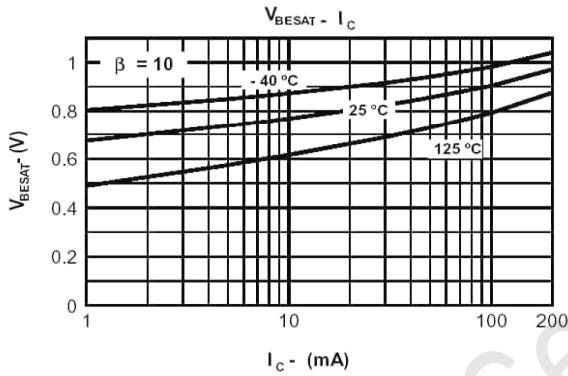
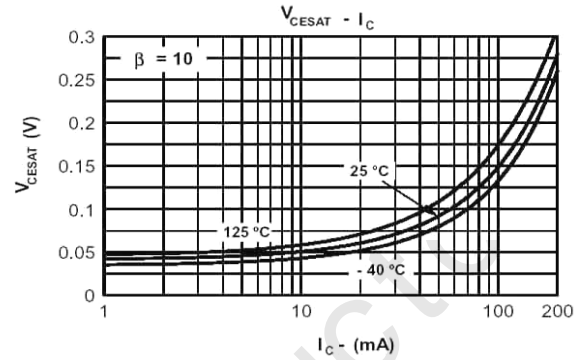
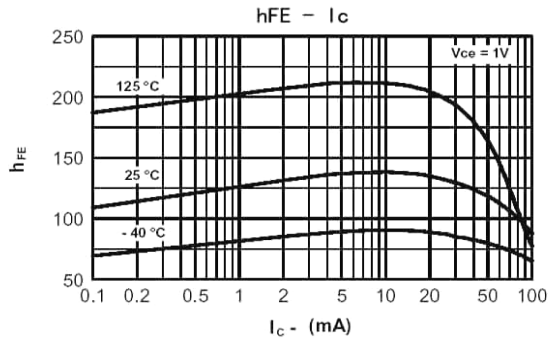
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

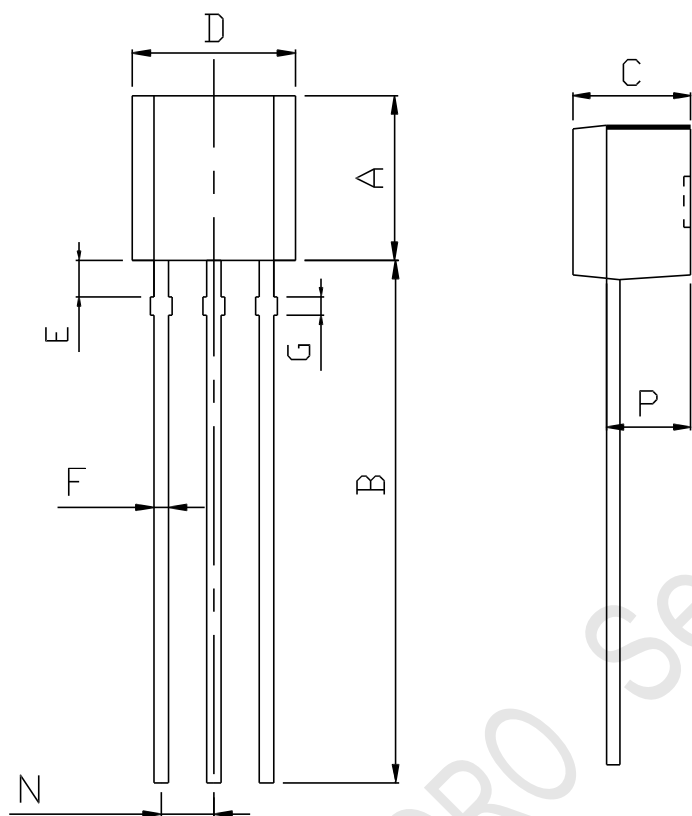
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\mu A$ $I_E = 0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -40V$ $I_E = 0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5.0V$ $I_C = 0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1.0V$ $I_C = -10mA$	100		300	
	$h_{FE(2)}$	$V_{CE} = -1.0V$ $I_C = -100mA$	30			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -50mA$ $I_B = -5.0mA$			-0.4	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -50mA$ $I_B = -5.0mA$			-0.95	V
Current Gain Bandwidth Product	f_T	$I_C = -10mA$ $V_{CE} = -20V$ $f = 100MHz$	250			MHz
Output Capacitance	C_{ob}	$V_{CB} = -5.0V$ $I_E = 0$ $f = 100KHz$			4.5	pF
Turn On Time	T_{on}	$V_{CC} = -3.0V$ $I_C = -10mA$ $V_{BE} = -0.5V$ $I_{B1} = -1.0mA$			0.07	μs
Turn Off Time	T_{off}	$V_{CC} = -3.0V$ $I_C = -10mA$ $I_{B1} = -I_{B2} = -1.0mA$			0.3	μs

电参数曲线图 / Electrical Characteristic Curve

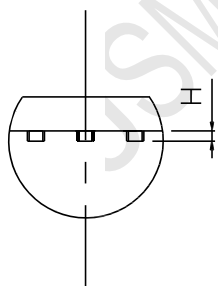


外形尺寸图 / Package Dimensions



DIM	MILLIMETERS
A	4.55±0.20
B	14.50±0.30
C	3.54±0.20
D	4.56±0.20
E	1.30±0.20
F	0.46±0.20
G	0.50±0.10
H	0.32±0.10
N	1.30±0.20
P	2.52±0.20

(Units: mm)



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